

Shalini Lal

List of Publications by Year in descending order

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Version: 2024-02-01

10
papers

82
citations

1937685

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1872680

6
g-index

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all docs

10
docs citations

10
times ranked

94
citing authors

#	ARTICLE	IF	CITATIONS
1	Engineering the (In, Al, Ga)N back-barrier to achieve high channel-conductivity for extremely scaled channel-thicknesses in N-polar GaN high-electron-mobility-transistors. Applied Physics Letters, 2014, 104, 092107.	3.3	26
2	Very high channel conductivity in ultra-thin channel N-polar GaN/(AlN, InAlN, AlGaIn) high electron mobility hetero-junctions grown by metalorganic chemical vapor deposition. Applied Physics Letters, 2013, 102, 232104.	3.3	19
3	Wafer-Bonded p-n Heterojunction of GaAs and Chemomechanically Polished N-Polar GaN. IEEE Electron Device Letters, 2013, 34, 42-44.	3.9	18
4	InGaAs-InGaN Wafer-Bonded Current Aperture Vertical Electron Transistors (BAVETs). Journal of Electronic Materials, 2012, 41, 857-864.	2.2	10
5	Barrier reduction via implementation of InGaN interlayer in wafer-bonded current aperture vertical electron transistors consisting of InGaAs channel and N-polar GaN drain. Applied Physics Letters, 2015, 106, .	3.3	4
6	Suppression of Anomalously Large Threshold Voltage in Wafer-Bonded Vertical Transistors by Enhancing Critical Field to Impact Ionization. IEEE Transactions on Electron Devices, 2018, 65, 1079-1086.	3.0	3
7	Controlling electronic properties of wafer-bonded interfaces among dissimilar materials: A path to developing novel wafer-bonded devices. , 2013, , .		1
8	Vertical electron transistors with $\text{In}_{0.53}\text{Ga}_{0.47}\text{As}$ channel and N-polar $\text{In}_{0.1}\text{Ga}_{0.9}\text{N}/\text{GaN}$ drain achieved by direct wafer-bonding. , 2014, , .		1
9	Experimental demonstration of a wafer-bonded heterostructure based unipolar transistor with $\text{In}_{0.53}\text{Ga}_{0.47}\text{As}$ channel and III-N drain. , 2012, , .		0
10	Controlling electronic properties of wafer-bonded interfaces among dissimilar materials: A path to developing novel wafer-bonded devices. , 2013, , .		0